

ABSTRACT

A resist pattern forming method which can prevent a fine resist pattern from collapsing in a drying step after a development treatment in case of forming a resist pattern is provided. This method comprises applying a positive resist composition comprising a resin component (A), which has an alkali-soluble unit content of less than 20 mol% and also has an acid dissociable dissolution inhibiting group, alkali solubility thereof being enhanced by action of acid, an acid generator component (B) which generates an acid under exposure, and an organic solvent (C) which dissolves the components (A) and (B) on a substrate; subjecting the resulting film to prebaking, selective exposure, post exposure baking and alkali development; performing a displacing step of displacing a liquid existing on the substrate with a displacing liquid at least one time; displacing the displacing liquid with a liquid for critical drying; and performing a drying step of drying the liquid for critical drying via a critical state.